

	Hits	Search Text	DBs
1	158	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((reduc\$4 or eliminat\$4 or decreas\$4) near14 ab\$2er\$2ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
2	1	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (high\$3 near9 index) same (low\$3 near9 index) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	1	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same ((high\$3 near9 index) or (low\$3 near9 index)) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	205	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	6	(("20050136334") or ("20040227923") or ("20040120458") or ("20020017922") or ("6583068") or ("6589717")) .PN.'	US-PGPUB; USPAT

	Hits	Search Text	DBs
6	106	(substrate or wafer or workpiece) and project\$4 and (lithographic\$5 or photolithographic\$5) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)) same (aluminum or Al))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	6	(substrate or wafer or workpiece) and project\$4 and (lithographic\$5 or photolithographic\$5) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((mask or (pattern\$4 near5 (device or structure)) or reticle) same (absorb\$4 or shield\$4 or antireflect\$4) same (aluminum or Al) same (protective or top\$3coat\$4 or (upper near5 layer) or (top near4 layer)) same (Al\$2O\$2 or ((Al or aluminum or Cr or chromium) near4 (oxide or nitride)) or Ru or ruthenium or Nb or niobium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	205	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	6	(substrate or wafer or workpiece) and project\$4 and (lithographic\$5 or photolithographic\$5) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((mask or (pattern\$4 near5 (device or structure)) or reticle) same (absorb\$4 or shield\$4 or antireflect\$4) same (aluminum or Al) same (protective or top\$3coat\$4 or (upper near5 layer) or (top near4 layer)) same (Al\$2O\$2 or ((Al or aluminum or Cr or chromium) near4 (oxide or nitride)) or Ru or ruthenium or Nb or niobium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	2	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((mask or (pattern\$4 near5 (device or structure)) or reticle) same (absorb\$4 or shield\$4 or antireflect\$4) same (aluminum or Al) same (protective or top\$3coat\$4 or (upper near5 layer) or (top near4 layer)) same (Al\$2O\$2 or ((Al or aluminum or Cr or chromium) near4 (oxide or nitride)) or Ru or ruthenium or Nb or niobium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
11	18	\$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((mask or (pattern\$4 near5 (device or structure)) or reticle) same (absorb\$4 or shield\$4 or antireflect\$4) same (protective or top\$3coat\$4 or (upper near5 layer) or (top near4 layer)) same ((buffer near5 layer) or SiO\$3 or (silicon near4 \$3oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	3	\$4lithograph\$5 and ((support or hold or stage or table) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((photomask or mask or (pattern\$4 near5 (device or structure)) or reticle) same (support\$4 or stage or hold\$4) same (absorb\$4 or shield\$4 or antireflect\$4) same (protective or top\$3coat\$4 or (upper near5 layer) or (top near4 layer)) same ((buffer near5 layer) or SiO\$3 or (silicon near4 \$4oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	563	\$4lithograph\$5 and ((support or hold or stage or table) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and (project\$4 same pattern\$4) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((photomask or mask or (pattern\$4 near5 (device or structure)) or reticle) same (support\$4 or stage or hold\$4) same (absorb\$4 or shield\$4 or antireflect\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	41	\$4lithograph\$5 and ((mask or reticle or pattern\$4 or photomask) same (low near5 ((refractive near5 index) or index)) same (high near5 ((refractive near6 index) or index)) same ((intermediate or barrier or between) near14 (film or layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	44	\$4lithograph\$5 and ((mask or reticle or pattern\$4 or photomask) same (low near14 ((refract\$4 near8 index) or index)) same (high near14 ((refract\$4 near8 index) or index)) same ((intermediate or barrier or between or (prevent near9 diffus\$4) or B\$2C) near14 (film or layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	383	\$4lithograph\$5 and ((low near14 ((refract\$4 near8 index) or index)) same (high near14 ((refract\$4 near8 index) or index)) same ((intermediate or barrier or between or anti\$4diffus\$4 or interface or (prevent near9 diffus\$4)) near14 (film or layer or B\$2C or (boron near4 carbide) or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	342	S19 NOT S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	223	S20 and (mask or reticle or photomask or (pattern\$4 near6 (device or structure)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
19	181	<p>\$4lithograph\$5 and ((low near14 ((refract\$4 near8 index) or index)) same (high near14 ((refract\$4 near8 index) or index)) same (alternat\$4 or multiple or pluralit\$3) same ((intermediate or barrier or between or anti\$4diffus\$4 or interface or (prevent near9 diffus\$4)) near14 (film or layer or B\$2C or (boron near4 carbide) or dielectric)))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>
20	49	<p>430/311.ccls. and \$4lithograph\$5 and ((support or hold or stage or table) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and (project\$4 same pattern\$4) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((photomask or mask or (pattern\$4 near5 (device or structure)) or reticle) same (support\$4 or stage or hold\$4) same (absorb\$4 or shield\$4 or antireflect\$4))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
21	14	430/5.ccls. and \$4lithograph\$5 and ((low near14 ((refract\$4 near8 index) or index)) same (high near14 ((refract\$4 near8 index) or index)) same ((intermediate or barrier or between or anti\$4diffus\$4 or interface or (prevent near9 diffus\$4)) near14 (film or layer or B\$2C or (boron near4 carbide) or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	10	355/18.ccls. and \$4lithograph\$5 and ((support or hold or stage or table) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and (project\$4 same pattern\$4) and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4 or layer) near5 (stack or layer)) or (low near4 (index or RI or (refractive near3 index)) near9 high))) and ((photomask or mask or (pattern\$4 near5 (device or structure)) or reticle) same (support\$4 or stage or hold\$4) same (absorb\$4 or shield\$4 or antireflect\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
23	8	430/396.ccls. and \$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	14	430/5.ccls. and \$4lithograph\$5 and ((low near14 ((refract\$4 near8 index) or index)) same (high near14 ((refract\$4 near8 index) or index)) same ((intermediate or barrier or between or anti\$4diffus\$4 or interface or (prevent near9 diffus\$4)) near14 (film or layer or B\$2C or (boron near4 carbide) or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	13	430/311.ccls. and \$4lithograph\$5 and ((support or hold or stage) same (expos\$4 or illuminat\$4 or irradiat\$4) same (mask or photomask or reticle or (pattern\$4 near5 (device or structure))) same (substrate or wafer or workpiece)) and project\$4 and ((mask or reticle or pattern\$4 or photomask) same (shield\$4 or absorb\$4 or ((multi\$4layer or alternat\$4) near5 (stack or layer)) or (low near4 index near9 high near9 alternat\$4))) and ((absorb\$4 or shield\$4 or antireflect\$4) same (multi\$3layer or stack or (alternat\$5 near3 layer) or (pluralit\$4 near layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB